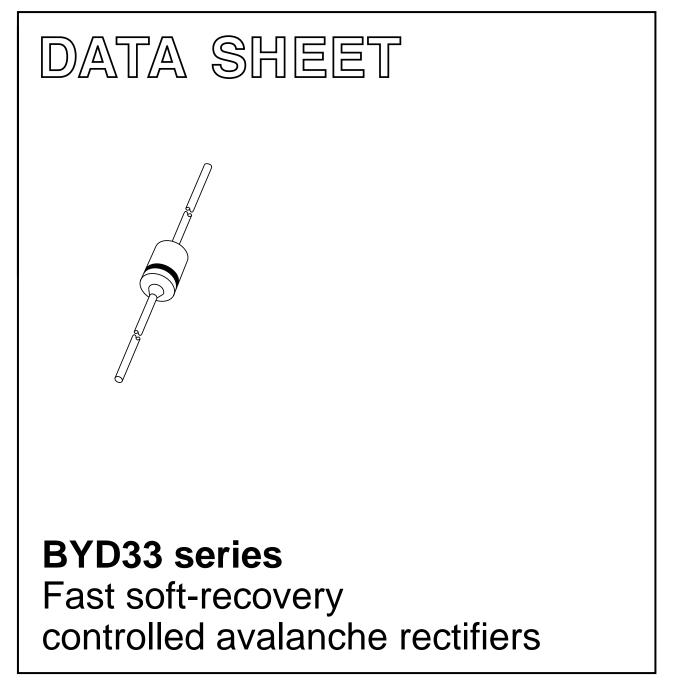
## DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 1996 Jun 05 File under Discrete Semiconductors, SC01 1996 Sep 18



#### **Product specification**

**BYD33 series** 

## Fast soft-recovery controlled avalanche rectifiers

#### FEATURES

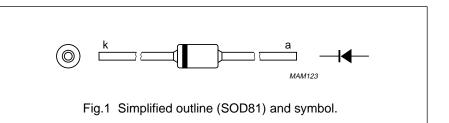
- Glass passivated
- High maximum operating temperature
- · Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability
- Available in ammo-pack.

#### DESCRIPTION

Cavity free cylindrical glass package through Implotec<sup>™(1)</sup> technology. This package is hermetically sealed

and fatigue free as coefficients of expansion of all used parts are matched.

(1) Implotec is a trademark of Philips.



#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>RRM</sub>	repetitive peak reverse voltage				
	BYD33D		_	200	V
	BYD33G		_	400	V
	BYD33J		_	600	V
	ВҮДЗЗК		_	800	V
	BYD33M		_	1000	V
	BYD33U		-	1200	V
	BYD33V		-	1400	V
V <sub>R</sub>	continuous reverse voltage				
	BYD33D		_	200	V
	BYD33G		_	400	V
	BYD33J		_	600	V
	ВҮДЗЗК		_	800	V
	BYD33M		_	1000	V
	BYD33U		-	1200	V
	BYD33V		_	1400	V
I <sub>F(AV)</sub>	average forward current	$T_{tp} = 55 \ ^{\circ}C$ ; lead length = 10 mm;			
	BYD33D to M	see Figs 2 and 3;	_	1.30	A
	BYD33U and V	averaged over any 20 ms period; see also Figs 10 and 11	-	1.26	A
I <sub>F(AV)</sub>	average forward current	T <sub>amb</sub> = 65 °C; PCB mounting (see			
	BYD33D to M	Fig.19); see Figs 4 and 5;	-	0.70	A
	BYD33U and V	averaged over any 20 ms period; see also Figs 10 and 11	-	0.67	A
I <sub>FRM</sub>	repetitive peak forward current	$T_{tp}$ = 55 °C; see Figs 6 and 7			
	BYD33D to M		-	12	A
	BYD33U and V		-	11	A

### BYD33 series

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>FRM</sub>	repetitive peak forward current	$T_{amb} = 65 \ ^{\circ}C$ ; see Figs 8 and 9			
	BYD33D to M		_	7	A
	BYD33U and V		_	6	A
I <sub>FSM</sub>	non-repetitive peak forward current	t = 10 ms half sine wave;	_	20	А
		$T_j = T_{j max}$ prior to surge; $V_R = V_{RRMmax}$			
E <sub>RSM</sub>	non-repetitive peak reverse avalanche energy	L = 120 mH; $T_j = T_{j max}$ prior to surge; inductive load switched off			
	BYD33D to J		_	10	mJ
	BYD33K to V		_	7	mJ
T <sub>stg</sub>	storage temperature		-65	+175	°C
Tj	junction temperature	see Figs 12 and 13	-65	+175	°C

### ELECTRICAL CHARACTERISTICS

 $T_j$  = 25  $^\circ C$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>F</sub>	forward voltage	$I_F = 1 A; T_j = T_{j max};$ see Figs 14 and 15	_	_	1.1	V
		I <sub>F</sub> = 1 A; see Figs 14 and 15	_	_	1.3	V
V <sub>(BR)R</sub>	reverse avalanche breakdown voltage	I <sub>R</sub> = 0.1 mA				
	BYD33D		300	_	-	V
	BYD33G		500	_	-	V
	BYD33J		700	_	-	V
	ВҮДЗЗК		900	_	-	V
	BYD33M		1100	_	-	V
	BYD33U		1300	-	-	V
	BYD33V		1500	-	-	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = V <sub>RRMmax</sub> ; see Fig.16	-	-	1	μA
		V <sub>R</sub> = V <sub>RRMmax</sub> ; T <sub>j</sub> = 165 °C; see Fig.16	-	_	100	μA
t <sub>rr</sub>	reverse recovery time	when switched from				
	BYD33D to J	$I_F = 0.5 \text{ A to } I_R = 1 \text{ A};$ measured at $I_R = 0.25 \text{ A}$ see Fig.21	-	_	250	ns
	BYD33K and M		-	_	300	ns
	BYD33U and V	000119.21	_	_	500	ns
C <sub>d</sub>	diode capacitance	$f = 1 MHz; V_R = 0 V;$ see Figs 17 and 18	_	20	-	pF

### BYD33 series

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$\left \frac{dI_R}{dt}\right $	maximum slope of reverse recovery current BYD33D to J BYD33K to V	when switched from $I_F = 1 A$ to $V_R \ge 30 V$ and $dI_F/dt = -1 A/\mu s$ ; see Fig.20	_	_	6 5	A/μs A/μs

#### THERMAL CHARACTERISTICS

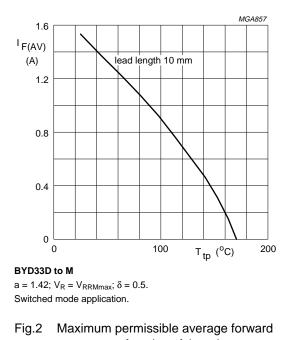
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point	lead length = 10 mm	60	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	120	K/W

Note

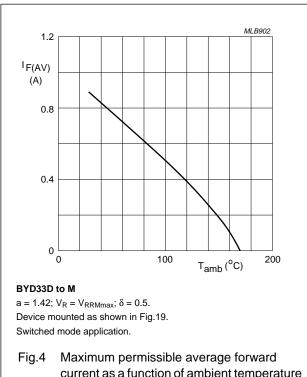
1. Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer ≥40 μm, see Fig.19. For more information please refer to the *'General Part of Handbook SC01'*.

### **BYD33** series

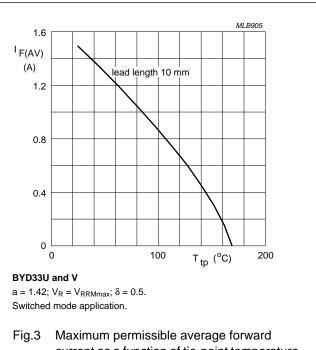
#### **GRAPHICAL DATA**



current as a function of tie-point temperature (including losses due to reverse leakage).



current as a function of ambient temperature (including losses due to reverse leakage).



current as a function of tie-point temperature (including losses due to reverse leakage).

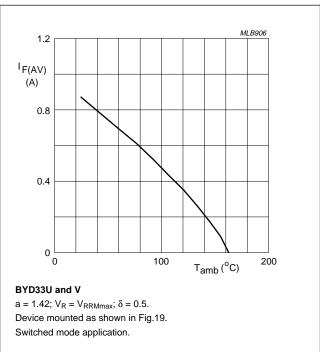
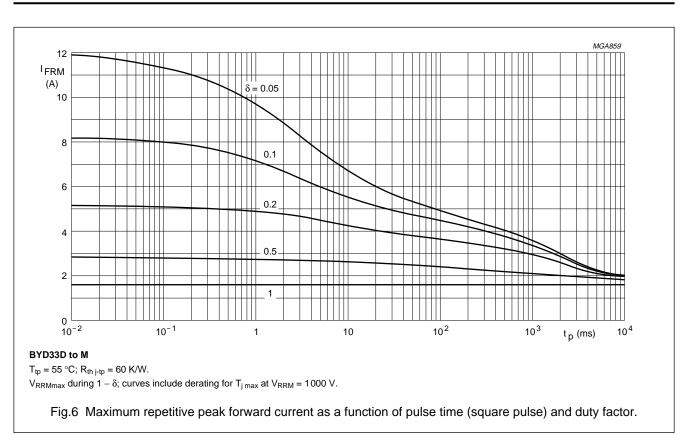


Fig.5 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).

## BYD33 series



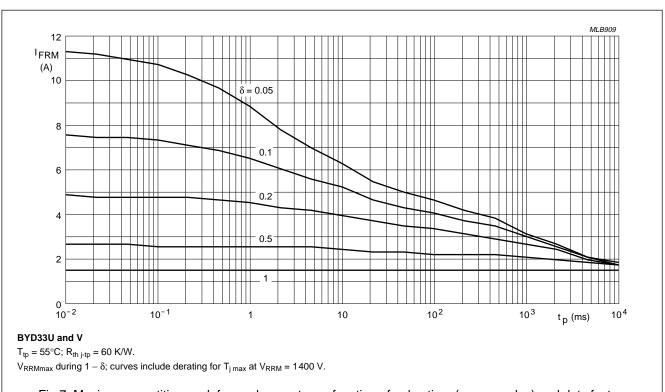
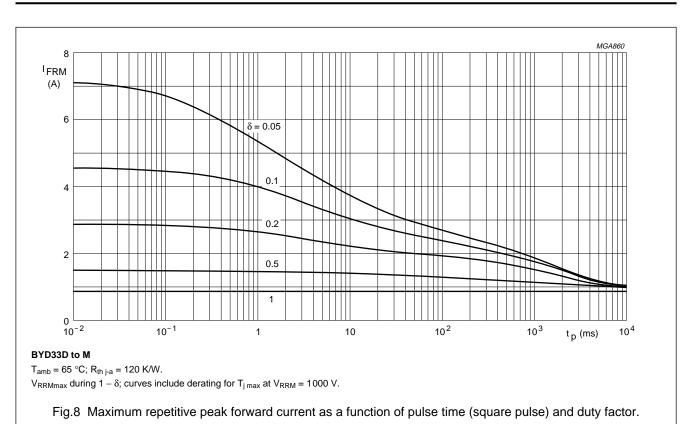


Fig.7 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

## **BYD33** series



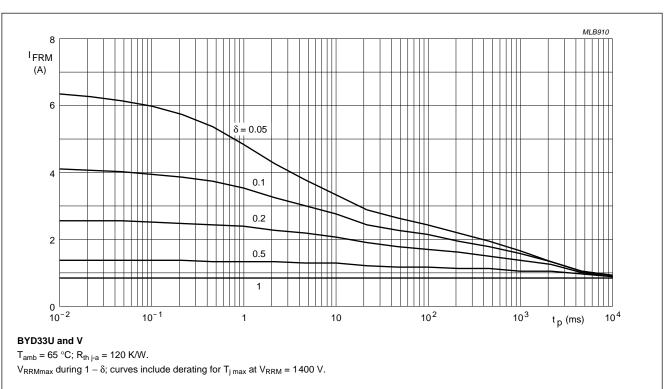
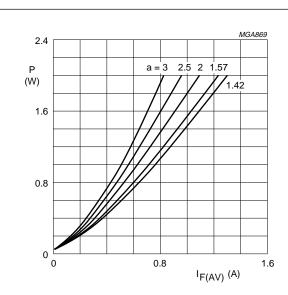


Fig.9 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

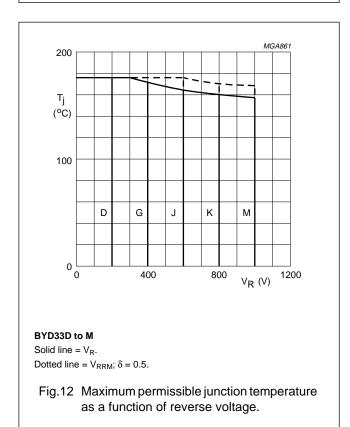
## **BYD33 series**

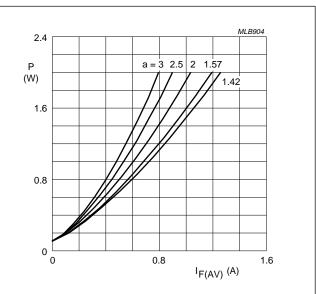


#### BYD33D to M

 $a = I_{F(RMS)}/I_{F(AV)}; V_{R} = V_{RRMmax}; \delta = 0.5.$ 

Fig.10 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.

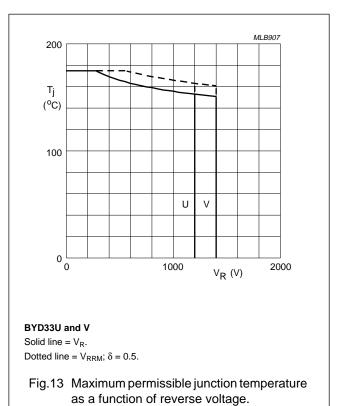




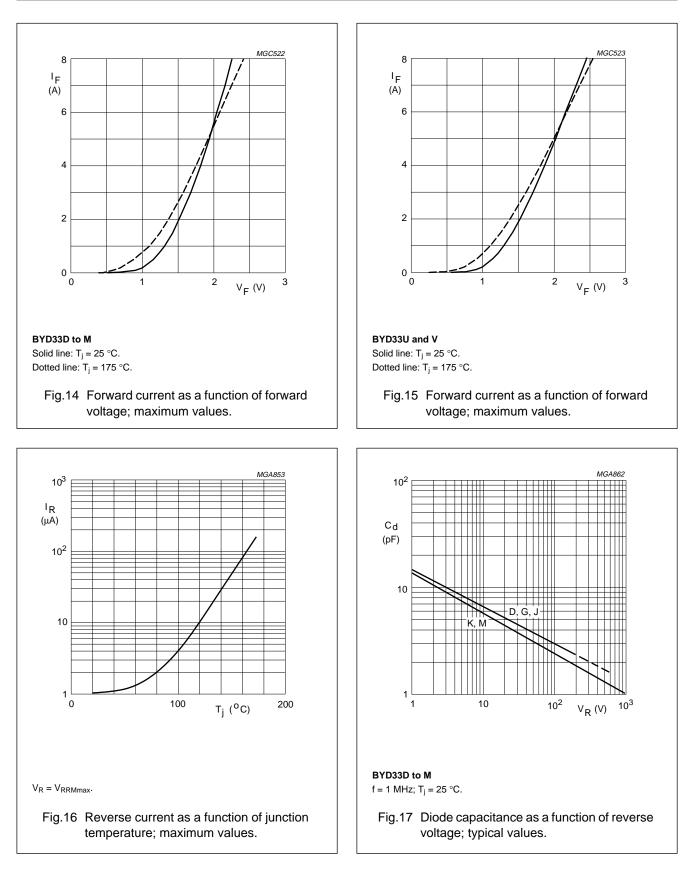
#### BYD33U and V

 $a = I_{F(RMS)}/I_{F(AV)}; \ V_R = V_{RRMmax}; \ \delta = 0.5. \label{eq:result}$ 

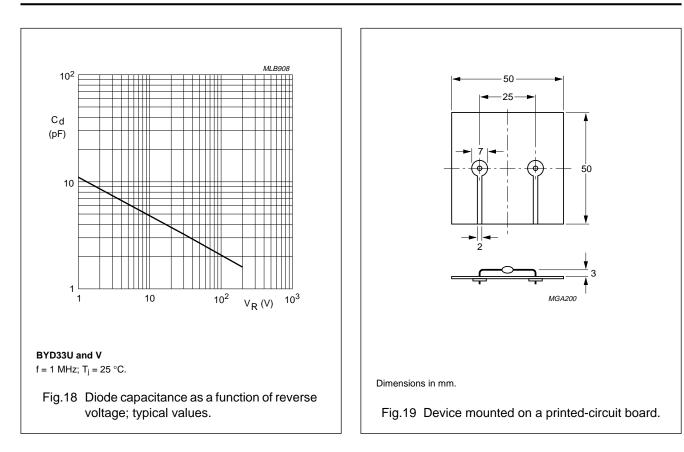
Fig.11 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.

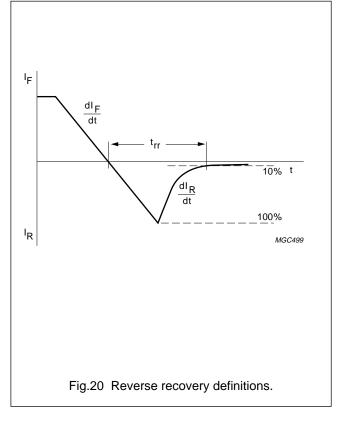


## **BYD33 series**

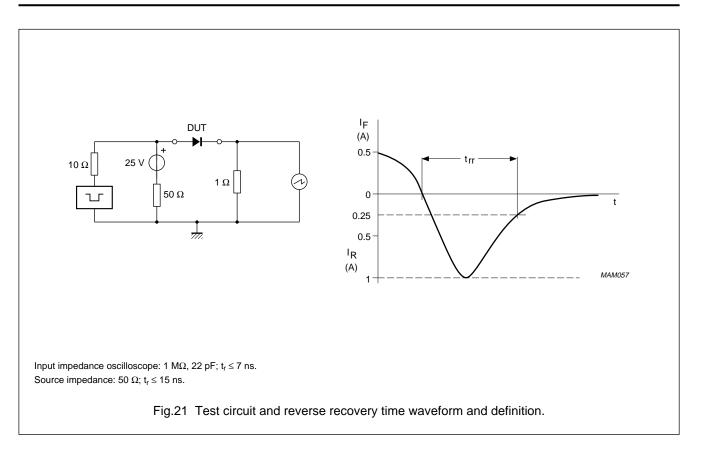


## BYD33 series



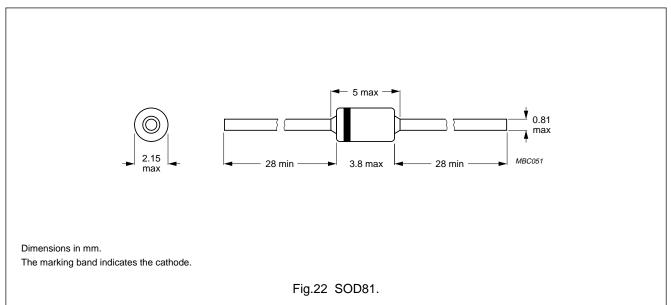


## **BYD33 series**



## **BYD33** series

#### PACKAGE OUTLINE



#### DEFINITIONS

Data Sheet Status				
Objective specification This data sheet contains target or goal specifications for product development.				
Preliminary specification	Preliminary specification This data sheet contains preliminary data; supplementary data may be published late			
Product specification	This data sheet contains final product specifications.			
Limiting values				
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.				
Application information				
Where application information is given, it is advisory and does not form part of the specification.				

#### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.